

## Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
20V	75mΩ@4.5V	1.2A
	90mΩ@2.5V	

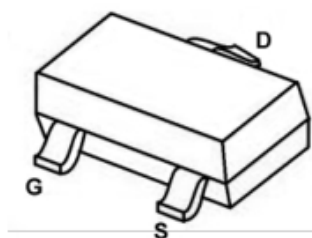
## Feature

- TrenchFET Power MOSFET
- Excellent  $R_{DS(on)}$  and Low Gate Charge

## Applications

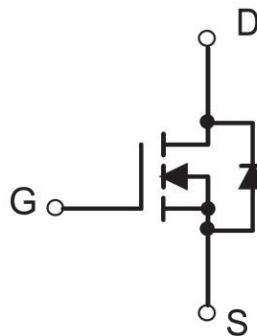
- DC/DC Converter
- Load Switch for Portable Devices
- Battery Switch

## Package

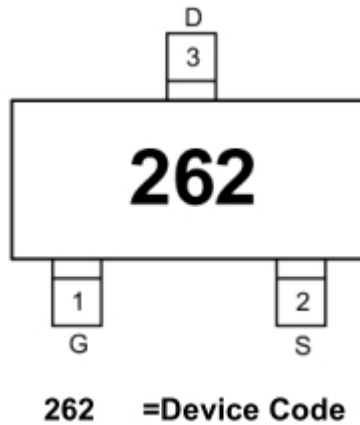


**SOT-323**

## Circuit diagram



## Marking



## Absolute maximum ratings

(T<sub>a</sub>=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±12	V
Continuous Drain Current	I <sub>D</sub>	1.2	A
Pulsed Drain Current	I <sub>DM</sub>	4.8	A
Power Dissipation	P <sub>D</sub>	0.2	W
Thermal Resistance from Junction to Ambient	R <sub>θJA</sub>	625	°C/W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>STG</sub>	-55~ +150	°C

## Electrical characteristics

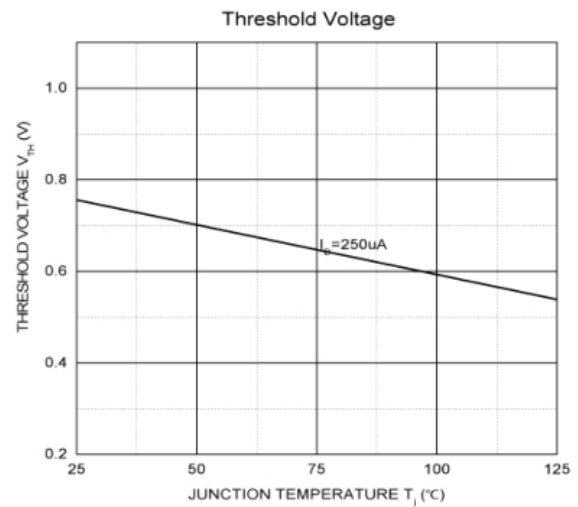
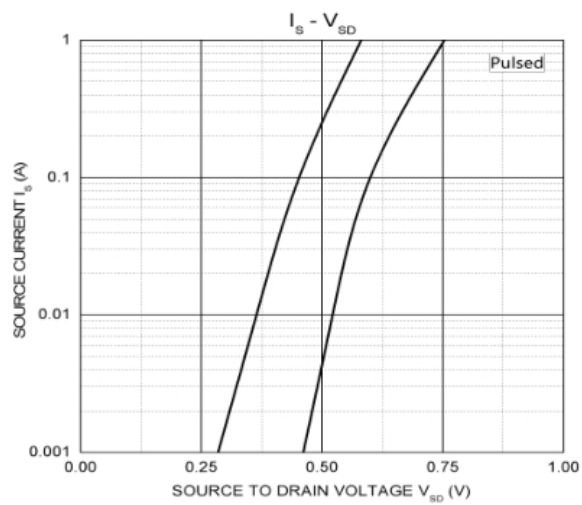
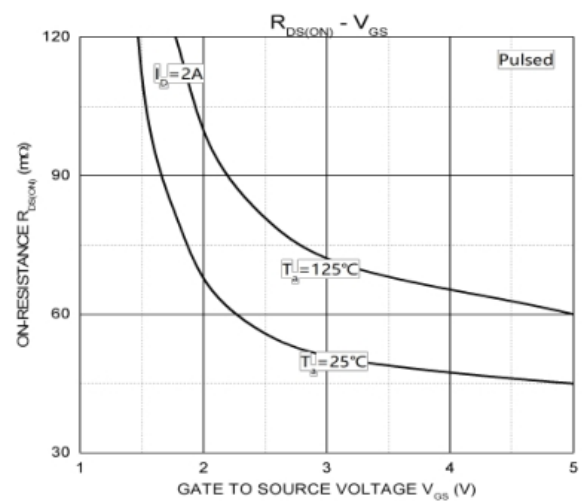
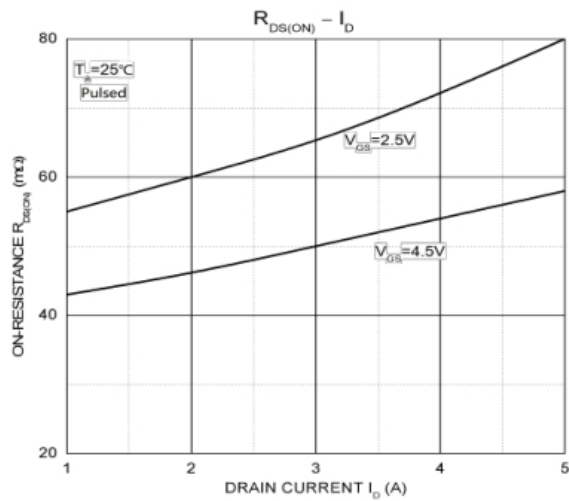
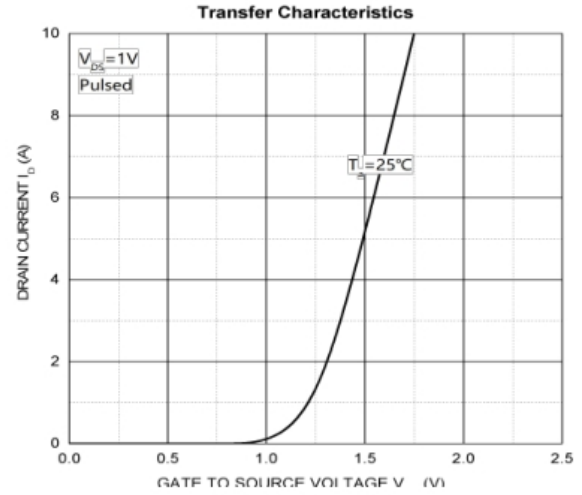
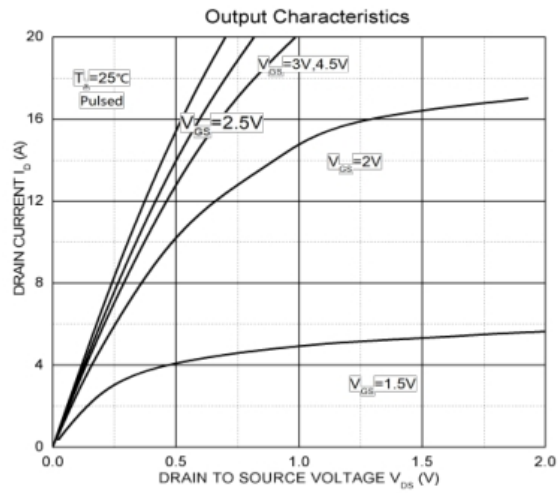
( $T_A=25^{\circ}\text{C}$ , unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source breakdown voltage	BV (BR)DSS	V <sub>GS</sub> = 0V, I <sub>D</sub> =250μA	20			V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> = 0V			1	uA
Gate-body leakage current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> = 0V			±0.1	uA
Gate threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.4	0.65	1	V
Drain-source on-resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =1A		75	90	mΩ
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =0.5A		90	110	
Dynamic Characteristics <sup>4)</sup>						
Input capacitance	C <sub>iSS</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =0V, f=1MHz		220		pF
Output capacitance	C <sub>OSS</sub>			40		
Reverse transfer capacitance	C <sub>rSS</sub>			20		
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A		2.7		nC
Gate-source charge	Q <sub>gs</sub>			0.4		
Gate-drain charge	Q <sub>gd</sub>			0.5		
Switching Characteristics <sup>4)</sup>						
Turn-on Delay Time	T <sub>d(on)</sub>	V <sub>DD</sub> =10V, R <sub>L</sub> =3.3Ω, V <sub>GEN</sub> =4.5V, R <sub>GEN</sub> =6Ω		2.3		nS
Turn-on Rise Time	T <sub>r</sub>			3.1		
Turn-Off Delay Time	T <sub>d(off)</sub>			20		
Turn-Off Fall Time	t <sub>f</sub>			2.5		
Source-Drain Diode Characteristics <sup>4)</sup>						
Diode Forward voltage	V <sub>SD</sub>	I <sub>S</sub> =1A, V <sub>GS</sub> =0V			1.2	V

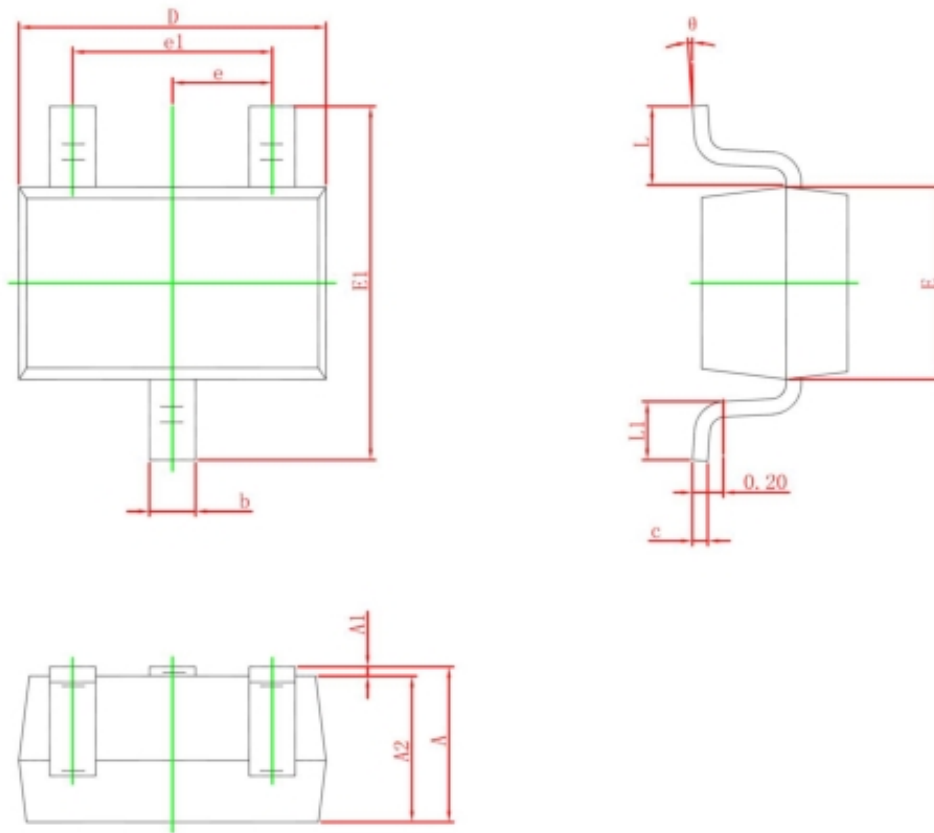
### Notes:

1. Pulse Test: Pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
2. These parameters have no way to verify.

## Typical Characteristics



## SOT-323 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.000	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
$\theta$	0°	8°	0°	8°